



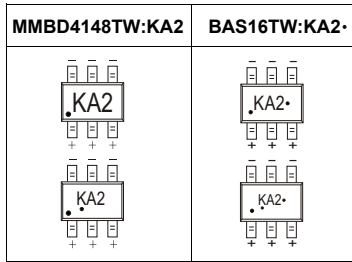
SOT-363 Plastic-Encapsulate Diodes

BAS16TW/MMBD4148TW SWITCHING DIODE

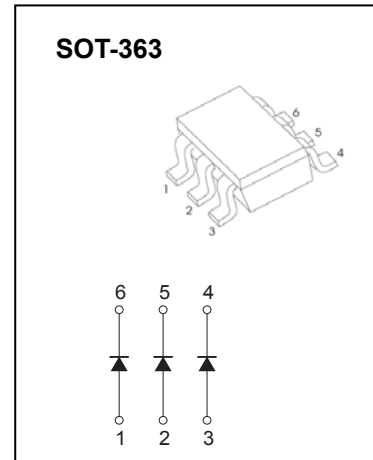
FEATURES

- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance

MARKING:



Solid dot = Pin1 indicate.
 Solid dot = Green molding compound device, if none, the normal device.



Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Peak Repetitive Peak Reverse Voltage	V_{RRM}	75	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R	53	V
RMS Reverse Voltage	$V_{R(RMS)}$		
Forward Continuous Current	I_{FM}	300	mA
Average Rectified Output Current	I_O	150	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}	2.0	A
Power Dissipation	P_d	200	mW
Thermal Resistance Junction to Ambient	R_{JA}	625	°C/W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{STG}	-55~+150	°C

Electrical Ratings @Ta=25°C

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse breakdown voltage	$V_{(BR)}$	75			V	$I_R=10 \text{ A}$
Forward voltage	V_{F1}			0.715	V	$I_F=1\text{mA}$
	V_{F2}			0.855	V	$I_F=10\text{mA}$
	V_{F3}			1.0	V	$I_F=50\text{mA}$
	V_{F4}			1.25	V	$I_F=150\text{mA}$
Reverse current	I_{R1}			1	A	$V_R=75\text{V}$
	I_{R2}			25	nA	$V_R=20\text{V}$
Capacitance between terminals	C_T			2	pF	$V_R=0\text{V}, f=1\text{MHz}$
Reverse recovery time	t_{rr}			4	ns	$I_F=I_R=10\text{mA}$ $0.1 \times I_R, R_L=100$

Typical Characteristics

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NOTICE

JCET reserve the right to make modifications,enhancements, improvements, corrections or other

